

Highly insulated module with Trench/Fieldstop IGBT3 and emitter controlled 3 diode

Features

- Electrical features
 - $V_{CES} = 4500\text{ V}$
 - $I_{C\text{ nom}} = 1500\text{ A} / I_{CRM} = 3000\text{ A}$
 - High DC stability
 - High dynamic robustness
 - Low $V_{CE,sat}$
 - Trench IGBT 3
 - $V_{CE,sat}$ with positive temperature coefficient
 - High short-circuit capability
- Mechanical features
 - High creepage and clearance distances
 - ALSiC base plate for increased thermal cycling capability
 - Package with enhanced insulation of 10.4 kV AC 60 s
 - Package with CTI > 600
 - Isolated base plate



Potential applications

- High-power converters
- Medium-voltage converters
- Motor drives
- Multi-level inverter
- Traction drives

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

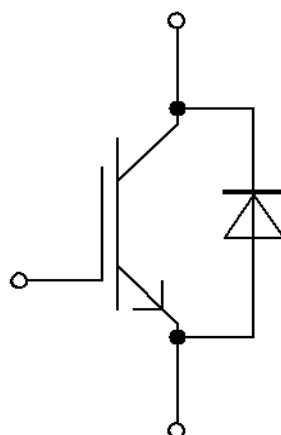


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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50 \text{ Hz}$, $t = 60 \text{ s}$	10.4	kV
Partial discharge extinction voltage	V_{isol}	RMS, $f = 50 \text{ Hz}$, $Q_{PD} \leq 10 \text{ pC}$	3.5	kV
DC stability	$V_{CE(D)}$	$T_{vj}=25^{\circ}\text{C}$, 100 Fit	3000	V
Material of module baseplate			AlSiC	
Internal isolation		basic insulation (class 1, IEC 61140)	AlN	
Creepage distance	d_{Creep}	terminal to heatsink	64.0	mm
Creepage distance	d_{Creep}	terminal to terminal	56.0	mm
Clearance	d_{Clear}	terminal to heatsink	40.0	mm
Clearance	d_{Clear}	terminal to terminal	26.0	mm
Comparative tracking index	CTI		> 600	

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{sCE}			18		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C=25^{\circ}\text{C}$, per switch		0.12		mΩ
Storage temperature	T_{stg}		-55		125	°C
Mounting torque for module mounting	M	- Mounting according to valid application note	M6, Screw	4.25	5.75	Nm
Terminal connection torque	M	- Mounting according to valid application note	M4, Screw	1.8	2.1	Nm
			M8, Screw	8	10	
Weight	G			1400		g

Note: The maximum allowed dv/dt measured between 0,6 and $1 \times V_{ce}$ is 1400V/μs.

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	V_{CES}	$T_{vj} = -40^{\circ}\text{C}$	4500	V
		$T_{vj} = 25^{\circ}\text{C}$	4500	
		$T_{vj} = 125^{\circ}\text{C}$	4500	

(table continues...)

Table 3 (continued) Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Continuous DC collector current	I_{CDC}	$T_{vj\ max} = 150\ ^\circ\text{C}$	$T_C = 80\ ^\circ\text{C}$	1500	A
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj\ op}$		3000	A
Gate-emitter peak voltage	V_{GES}			± 20	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 1500\ \text{A}, V_{GE} = 15\ \text{V}$	$T_{vj} = 25\ ^\circ\text{C}$		2.70	3.05	V
			$T_{vj} = 125\ ^\circ\text{C}$		3.25	3.85	
Gate threshold voltage	V_{GETh}	$I_C = 105\ \text{mA}, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ\text{C}$		5.40	6	6.60	V
Gate charge	Q_G	$V_{GE} = \pm 15\ \text{V}, V_{CC} = 2800\ \text{V}$			39.5		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ\text{C}$			0.75		Ω
Input capacitance	C_{ies}	$f = 1000\ \text{kHz}, T_{vj} = 25\ ^\circ\text{C}, V_{CE} = 25\ \text{V}, V_{GE} = 0\ \text{V}$			280		nF
Reverse transfer capacitance	C_{res}	$f = 1000\ \text{kHz}, T_{vj} = 25\ ^\circ\text{C}, V_{CE} = 25\ \text{V}, V_{GE} = 0\ \text{V}$			4.7		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 4500\ \text{V}, V_{GE} = 0\ \text{V}$	$T_{vj} = 25\ ^\circ\text{C}$			5	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ \text{V}, V_{GE} = 20\ \text{V}, T_{vj} = 25\ ^\circ\text{C}$				400	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 1500\ \text{A}, V_{CC} = 2800\ \text{V}, V_{GE} = \pm 15\ \text{V}, R_{Gon} = 0.68\ \Omega$	$T_{vj} = 25\ ^\circ\text{C}$		0.910		μs
			$T_{vj} = 125\ ^\circ\text{C}$		0.960		
Rise time (inductive load)	t_r	$I_C = 1500\ \text{A}, V_{CC} = 2800\ \text{V}, V_{GE} = \pm 15\ \text{V}, R_{Gon} = 0.68\ \Omega$	$T_{vj} = 25\ ^\circ\text{C}$		0.210		μs
			$T_{vj} = 125\ ^\circ\text{C}$		0.230		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 1500\ \text{A}, V_{CC} = 2800\ \text{V}, V_{GE} = \pm 15\ \text{V}, R_{Goff} = 6.2\ \Omega$	$T_{vj} = 25\ ^\circ\text{C}$		7.310		μs
			$T_{vj} = 125\ ^\circ\text{C}$		7.710		
Fall time (inductive load)	t_f	$I_C = 1500\ \text{A}, V_{CC} = 2800\ \text{V}, V_{GE} = \pm 15\ \text{V}, R_{Goff} = 6.2\ \Omega$	$T_{vj} = 25\ ^\circ\text{C}$		1.020		μs
			$T_{vj} = 125\ ^\circ\text{C}$		1.970		
Turn-on time (resistive load)	t_{on_R}	$I_C = 500\ \text{A}, V_{CC} = 2000\ \text{V}, V_{GE} = \pm 15\ \text{V}, R_{Gon} = 0.68\ \Omega$	$T_{vj} = 25\ ^\circ\text{C}$	1.73			μs
Turn-on energy loss per pulse	E_{on}	$I_C = 1500\ \text{A}, V_{CC} = 2800\ \text{V}, L_\sigma = 110\ \text{nH}, V_{GE} = \pm 15\ \text{V}, R_{Gon} = 0.68\ \Omega, di/dt = 5200\ \text{A}/\mu\text{s} (T_{vj} = 125\ ^\circ\text{C})$	$T_{vj} = 25\ ^\circ\text{C}$		5200		mJ
			$T_{vj} = 125\ ^\circ\text{C}$		7500		

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-off energy loss per pulse	E_{off}	$I_C = 1500\text{ A}$, $V_{CC} = 2800\text{ V}$, $L_\sigma = 110\text{ nH}$, $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 6.2\text{ }\Omega$, $dv/dt = 1300\text{ V}/\mu\text{s}$ ($T_{vj} = 125\text{ }^\circ\text{C}$)	$T_{vj} = 25\text{ }^\circ\text{C}$	6050		mJ
			$T_{vj} = 125\text{ }^\circ\text{C}$	7750		
SC data	I_{SC}	$V_{GE} \leq 15\text{ V}$, $V_{CC} = 2800\text{ V}$, $V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$	$t_p = 10\text{ }\mu\text{s}$, $T_{vj} = 125\text{ }^\circ\text{C}$	6900		A
Thermal resistance, junction to case	R_{thJC}	per IGBT			7.40	K/kW
Thermal resistance, case to heat sink	R_{thCH}	per IGBT, $\lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		9.00		K/kW
Temperature under switching conditions	$T_{vj\text{ op}}$		-50		125	$^\circ\text{C}$

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		$T_{vj} = -40\text{ }^{\circ}\text{C}$	4500	V
			$T_{vj} = 25\text{ }^{\circ}\text{C}$	4500	
			$T_{vj} = 125\text{ }^{\circ}\text{C}$	4500	
Continuous DC forward current	I_F			1500	A
Repetitive peak forward current	I_{FRM}	$t_P = 1\text{ ms}$		3000	A
I^2t - value	I^2t	$t_P = 10\text{ ms}$, $V_R = 0\text{ V}$	$T_{vj} = 125\text{ }^{\circ}\text{C}$	570	kA^2s
Maximum power dissipation	P_{RQM}		$T_{vj} = 125\text{ }^{\circ}\text{C}$	2400	kW
Minimum turn-on time	t_{onmin}			10	μs

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 1500\text{ A}$, $V_{GE} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$	2.80	3.40	V
			$T_{vj} = 125\text{ }^\circ\text{C}$	2.70	3.20	
Peak reverse recovery current	I_{RM}	$V_{CC} = 2800\text{ V}$, $I_F = 1500\text{ A}$, $V_{GE} = -15\text{ V}$, $-di_F/dt = 5200\text{ A}/\mu\text{s}$ ($T_{vj} = 125\text{ }^\circ\text{C}$)	$T_{vj} = 25\text{ }^\circ\text{C}$	1600		A
			$T_{vj} = 125\text{ }^\circ\text{C}$	1800		

(table continues...)

Table 6 (continued) Characteristic values

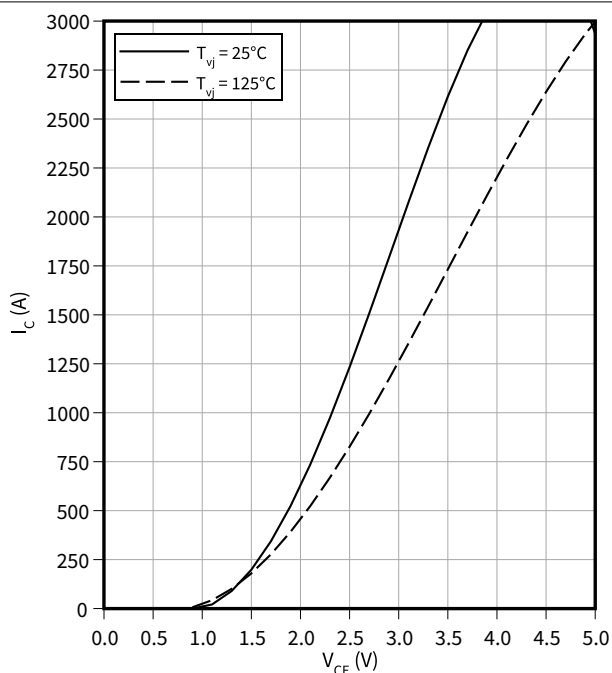
Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Recovered charge	Q_r	$V_{CC} = 2800 \text{ V}$, $I_F = 1500 \text{ A}$, $V_{GE} = -15 \text{ V}$, $-di_F/dt = 5200 \text{ A}/\mu\text{s}$ ($T_{vj} = 125 \text{ }^\circ\text{C}$)	$T_{vj} = 25 \text{ }^\circ\text{C}$		1300		μC
			$T_{vj} = 125 \text{ }^\circ\text{C}$		2500		
Reverse recovery energy	E_{rec}	$V_{CC} = 2800 \text{ V}$, $I_F = 1500 \text{ A}$, $V_{GE} = -15 \text{ V}$, $-di_F/dt = 5200 \text{ A}/\mu\text{s}$ ($T_{vj} = 125 \text{ }^\circ\text{C}$)	$T_{vj} = 25 \text{ }^\circ\text{C}$		2000		mJ
			$T_{vj} = 125 \text{ }^\circ\text{C}$		4300		
Thermal resistance, junction to case	R_{thJC}	per diode				17.0	K/kW
Thermal resistance, case to heat sink	R_{thCH}	per diode, $\lambda_{grease} = 1 \text{ W}/(\text{m}\cdot\text{K})$			14.0		K/kW
Temperature under switching conditions	$T_{vj\text{ op}}$			-50		125	$^\circ\text{C}$

4 Characteristics diagrams

Output characteristic (typical), IGBT, Inverter

$$I_C = f(V_{CE})$$

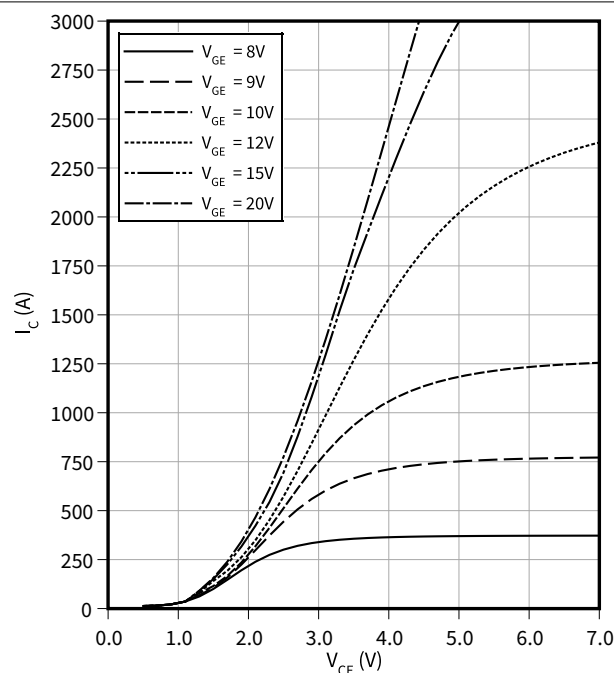
$$V_{GE} = 15 \text{ V}$$



Output characteristic field (typical), IGBT, Inverter

$$I_C = f(V_{CE})$$

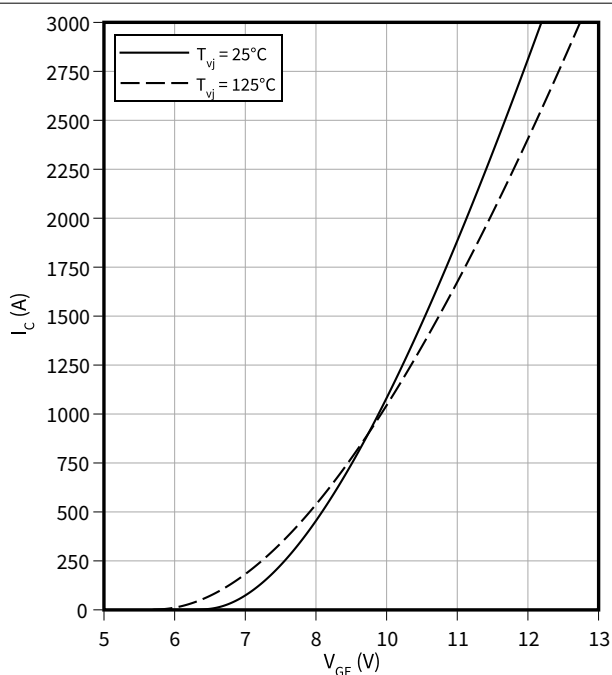
$$T_{vj} = 125 \text{ °C}$$



Transfer characteristic (typical), IGBT, Inverter

$$I_C = f(V_{GE})$$

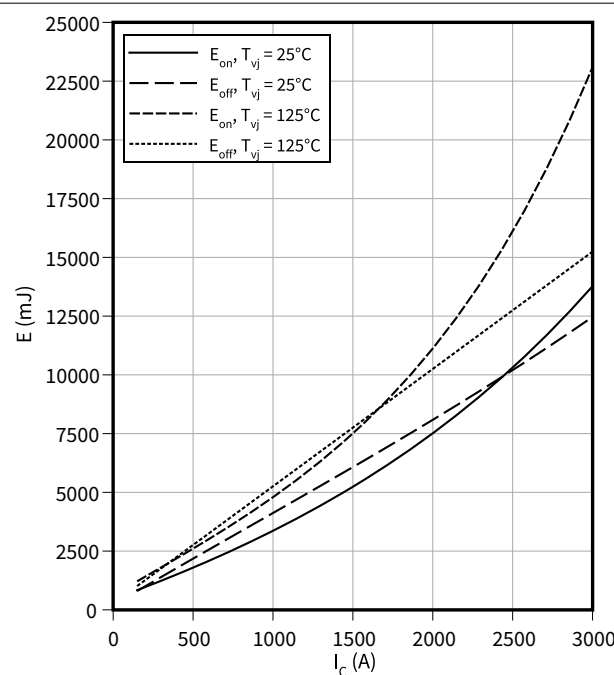
$$V_{CE} = 20 \text{ V}$$



Switching losses (typical), IGBT, Inverter

$$E = f(I_C)$$

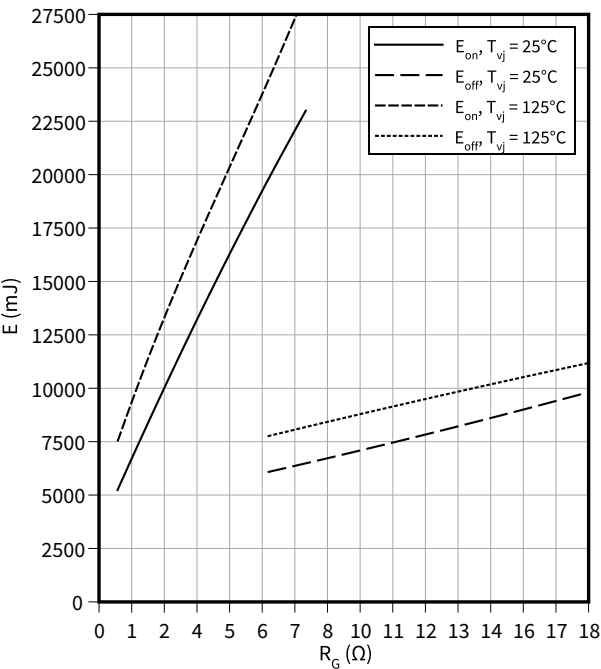
$$R_{Goff} = 6.2 \text{ } \Omega, R_{Gon} = 0.68 \text{ } \Omega, V_{CC} = 2800 \text{ V}, V_{GE} = -15 / 15 \text{ V}$$



4 Characteristics diagrams

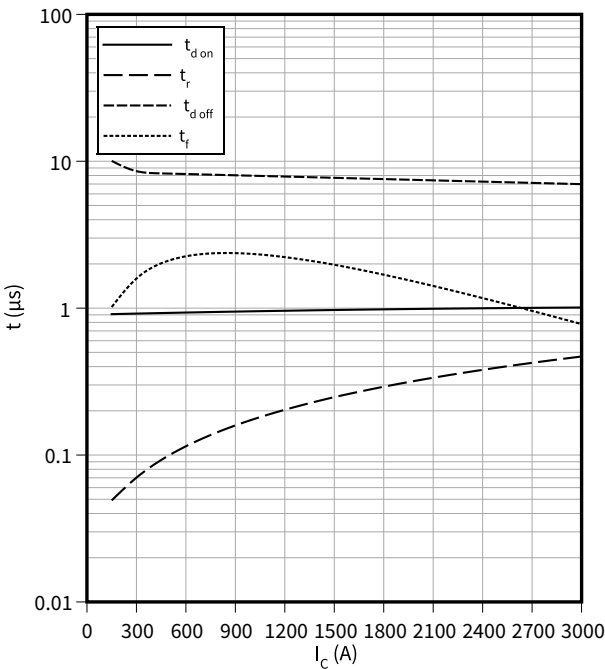
Switching losses (typical), IGBT, Inverter

$E = f(R_G)$
 $I_C = 1500\text{ A}$, $V_{CC} = 2800\text{ V}$, $V_{GE} = -15 / 15\text{ V}$



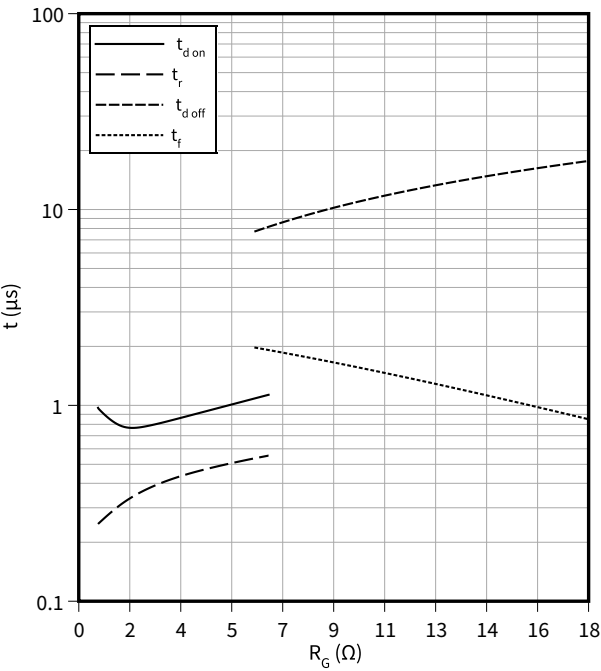
Switching times (typical), IGBT, Inverter

$t = f(I_C)$
 $R_{Goff} = 6.2\text{ }\Omega$, $R_{Gon} = 0.68\text{ }\Omega$, $V_{GE} = \pm 15\text{ V}$, $V_{CC} = 2800\text{ V}$, $T_{vj} = 125\text{ }^\circ\text{C}$



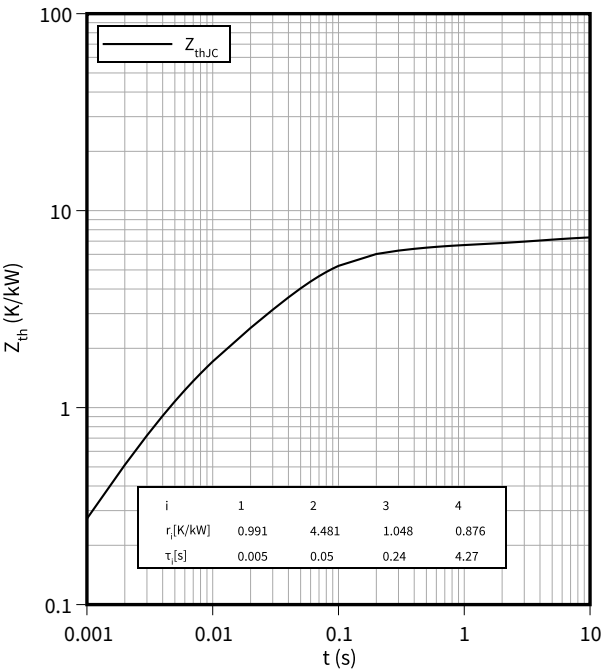
Switching times (typical), IGBT, Inverter

$t = f(R_G)$
 $V_{GE} = \pm 15\text{ V}$, $I_C = 1500\text{ A}$, $V_{CC} = 2800\text{ V}$, $T_{vj} = 125\text{ }^\circ\text{C}$



Transient thermal impedance , IGBT, Inverter

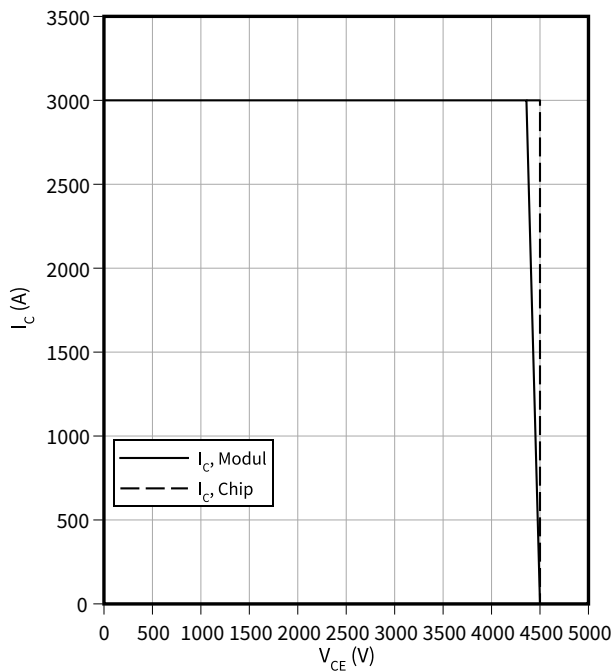
$Z_{th} = f(t)$



4 Characteristics diagrams

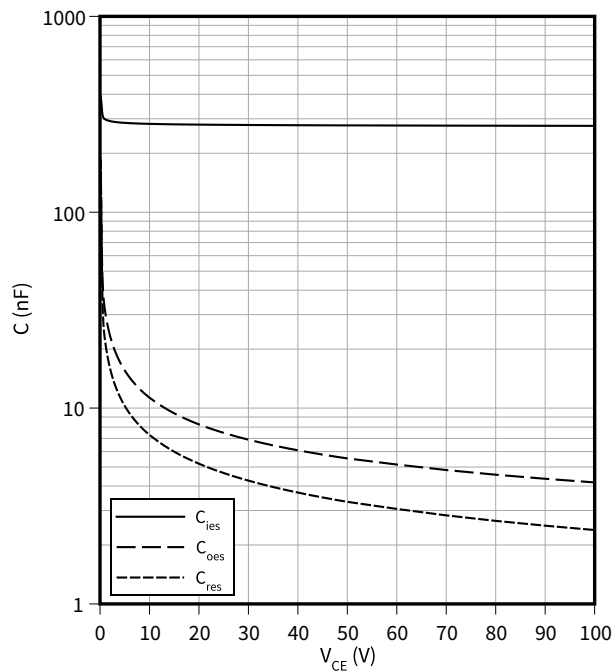
Reverse bias safe operating area (RBSOA), IGBT, Inverter

$I_C = f(V_{CE})$
 $R_{Goff} = 6.2 \Omega$, $V_{GE} = \pm 15 \text{ V}$, $T_{vj} = 125 \text{ }^\circ\text{C}$



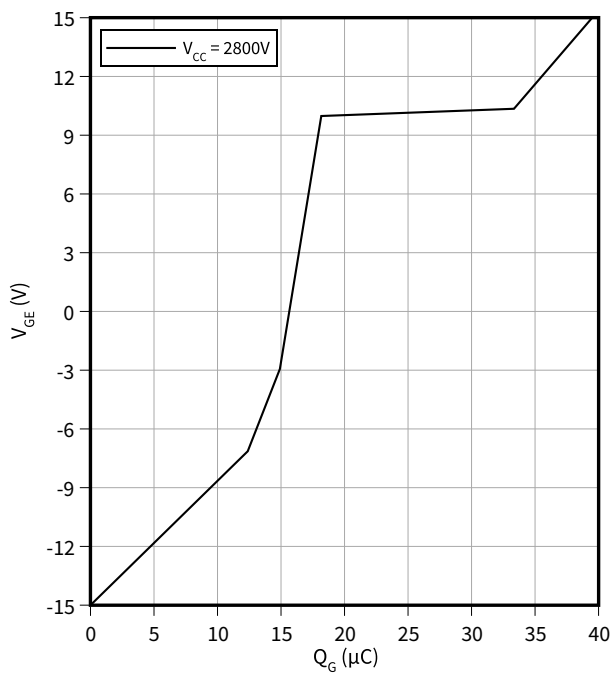
Capacity characteristic (typical), IGBT, Inverter

$C = f(V_{CE})$
 $f = 1000 \text{ kHz}$, $V_{GE} = 0 \text{ V}$, $T_{vj} = 25 \text{ }^\circ\text{C}$



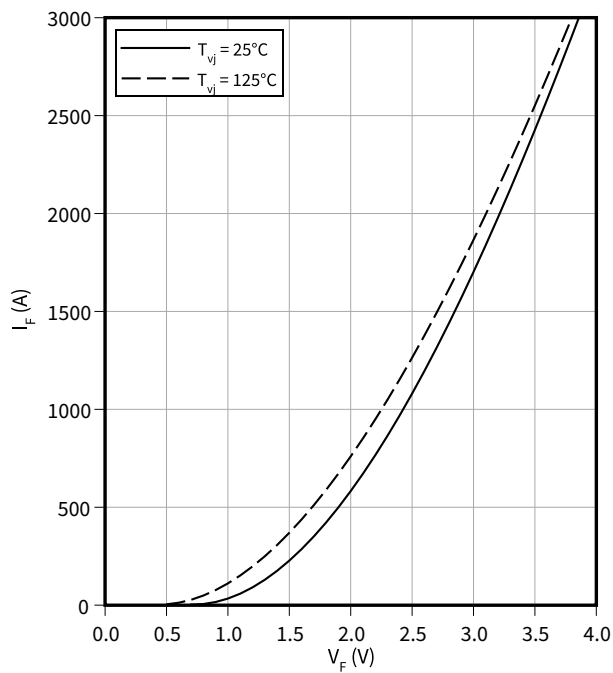
Gate charge characteristic (typical), IGBT, Inverter

$V_{GE} = f(Q_G)$
 $I_C = 1500 \text{ A}$, $T_{vj} = 25 \text{ }^\circ\text{C}$



Forward characteristic (typical), Diode, Inverter

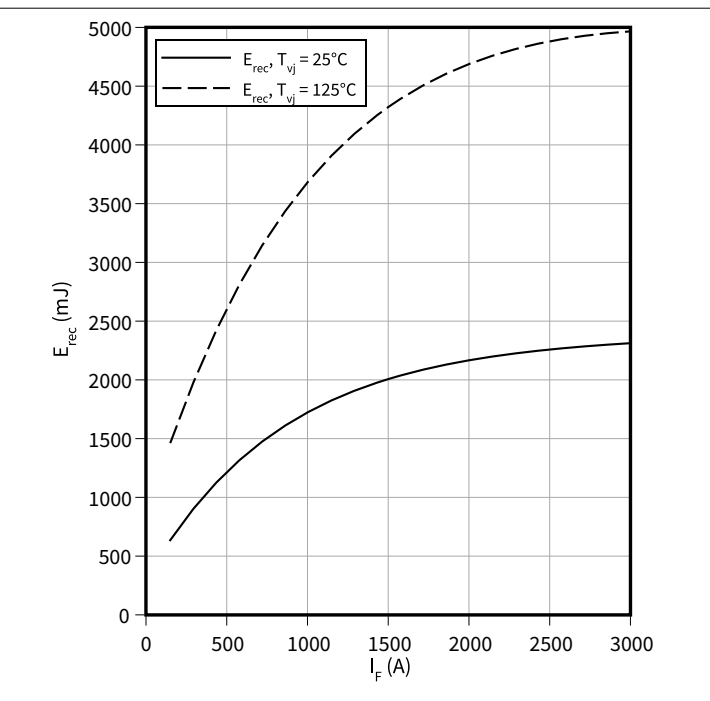
$I_F = f(V_F)$



4 Characteristics diagrams

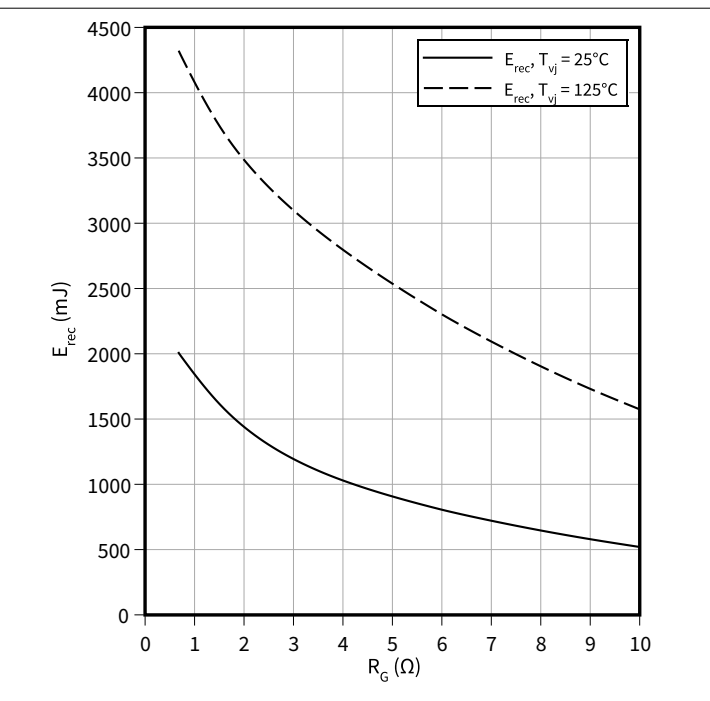
Switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$
 $R_{Gon} = R_{Gon}(IGBT)$, $V_{CC} = 2800\text{ V}$



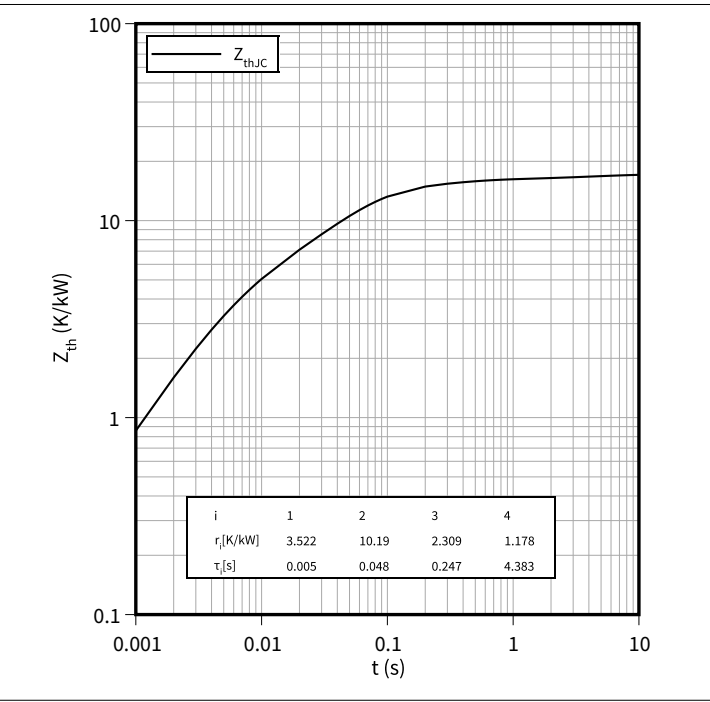
Switching losses (typical), Diode, Inverter

$E_{rec} = f(R_G)$
 $I_F = 1500\text{ A}$, $V_{CC} = 2800\text{ V}$



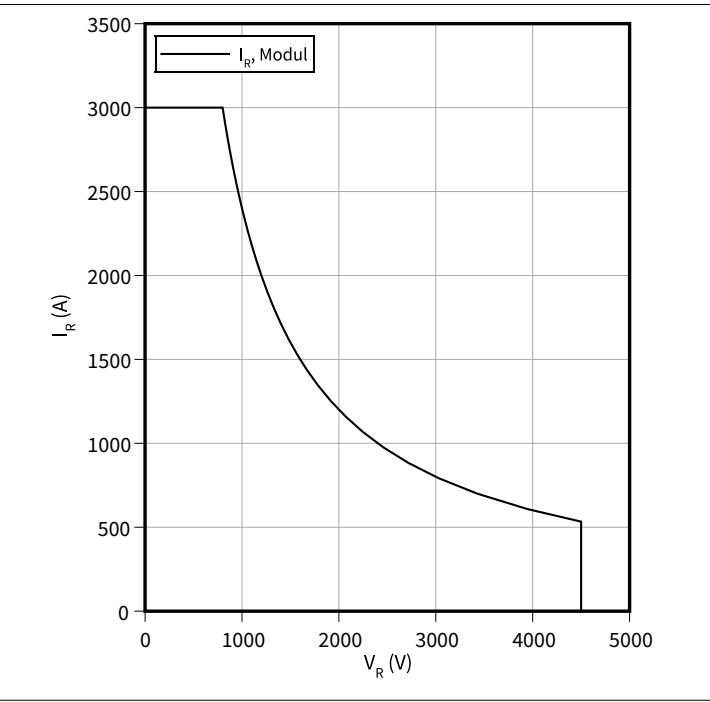
Transient thermal impedance, Diode, Inverter

$Z_{th} = f(t)$



Safe operating area (SOA), Diode, Inverter

$I_R = f(V_R)$
 $T_{vj} = 125\text{ °C}$



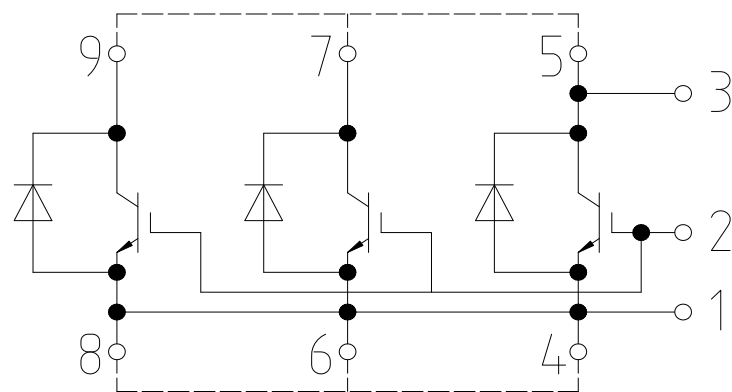


Figure 1

6 Package outlines

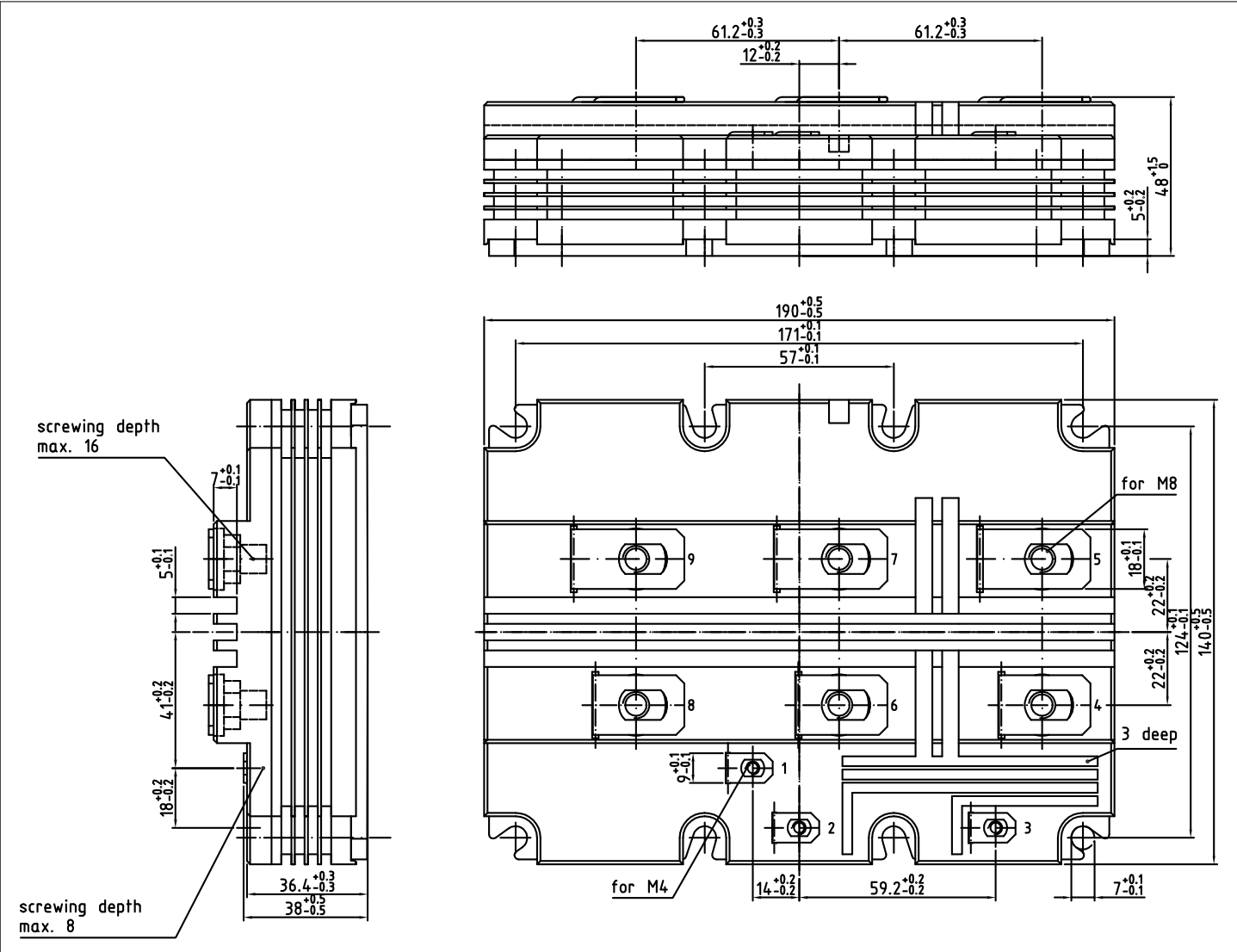


Figure 2

7 Module label code

Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	<i>Content</i>	<i>Digit</i>	<i>Example</i>
	Module serial number	1 – 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 – 21	15
	Date code (production week)	22 – 23	30
Example			
	 71549142846550549911530	 71549142846550549911530	

Figure 3

Revision history

Document revision	Date of release	Description of changes
0.10	2021-09-15	Initial version
0.20	2022-02-24	Target datasheet
0.30	2022-05-16	Preliminary datasheet
1.00	2022-08-15	Final datasheet

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